

SEMICONDUCTOR DEVICE AND FABRICATING METHOD THEREOF

ABSTRACT OF THE DISCLOSURE

Provided is an MRAM memory cell structure capable of preventing generation of parasitic transistors. Diodes are adopted as switching elements of an MRAM memory cell. An n-type semiconductor layer and a p-type semiconductor layer, which collectively constitute a diode, are formed on a surface semiconductor layer of an SOI substrate. The n-type semiconductor layer and the p-type semiconductor layer are disposed in a lateral direction and isolated by an isolation region, whereby the diode is isolated electrically from other elements and from the substrate.



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